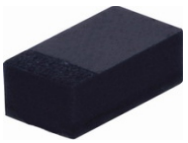
SMD Schottky Barrier Diode

COMCHIP
SMD Diodes Specialist

CDBFR0245 (RoHs Device)

Io = 200 mA
V_R = 45 Volts

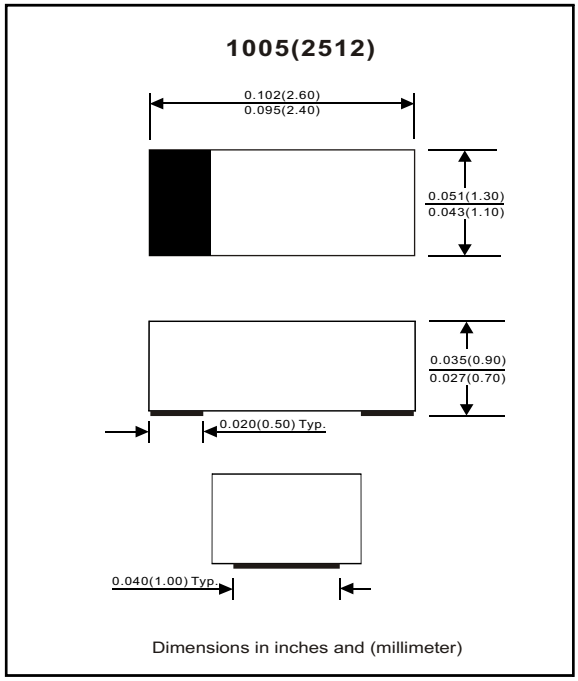


Features

- Designed for mounting on small surface.
- Extremely thin/leadless package.
- Low leakage current(I_R=0.1uA typ. @V_R=10V).
- Majority carrier conduction.

Mechanical data

- Case: 1005(2512) standard package, molded plastic.
- Terminals: Gold plated, solderable per MIL-STD-750,method 2026.
- Polarity: Indicated by cathode band.
- Mounting position: Any
- Weight: 0.006 gram(approx.).



Maximum Rating (at T_A=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive peak reverse voltage		V_{RRM}			50	V
Reverse voltage		V_R			45	V
Average forward current		I_O			200	mA
Forward current,surge peak	8.3ms single half sine-wave superimposed on rate load(JEDEC method)	I_{FSM}		3000		mA
Power Dissipation		P_D			250	mW
Storage temperature		T_{STG}	-40		+125	°C
Junction temperature		T_j	-40		+125	°C

Electrical Characteristics (at T_A=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F = 200 mA DC	V_F			0.55	V
Reverse current	V_R = 10 V	I_R			1	uA
Capacitance between terminals	f = 1 MHz, and 10VDC reverse voltage	C_T		9		pF

RATING AND CHARACTERISTIC CURVES (CDBFR0245)

Fig. 1 - Forward characteristics

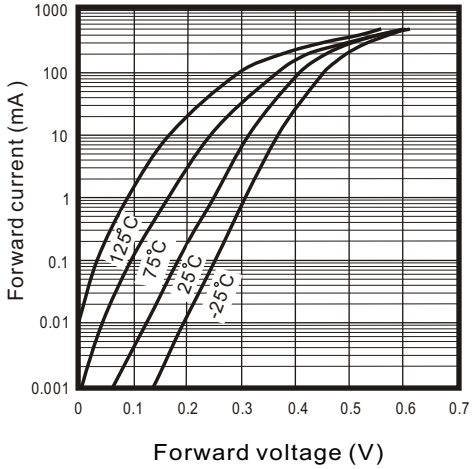


Fig. 2 - Reverse characteristics

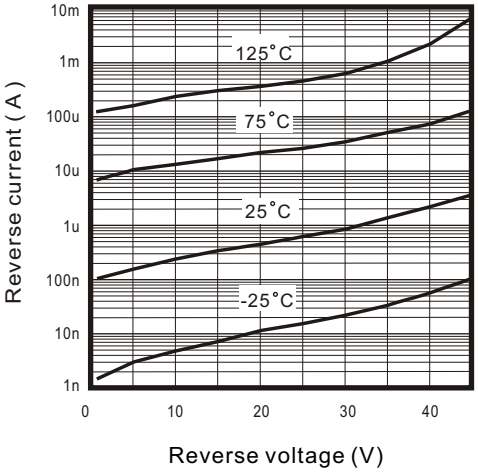


Fig. 3 - Capacitance between terminals characteristics

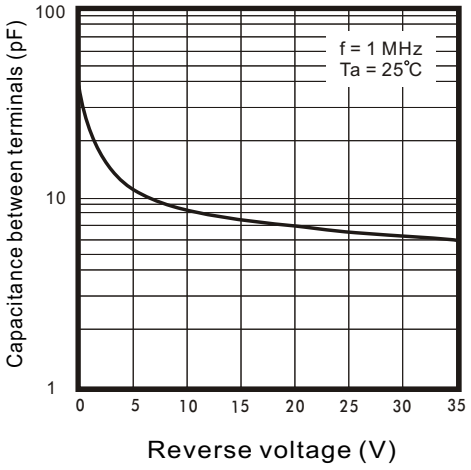


Fig. 4 - Current derating curve